structure; and

an active layer formed on the buffer layer and having an active element formed therein.

2. (Amended) The semiconductor device as claimed in claim 1, wherein the compound semiconductor substrate has a resistivity less than 0.6×10^8 Ohm-cm.

3. (Amended) The semiconductor device as claimed in claim 1, wherein the active layer is formed at a position within 5.0 μm from the surface of the compound semiconductor substrate.

4. (Amended) The semiconductor device as claimed in claim 1, further comprising an electrode layer formed on another surface of the compound semiconductor substrate.

5. (Amended) The semiconductor device as claimed in claim 4, wherein the electrode layer is not electrically connected to any power supply potential of the semiconductor device.

6. (Amended) The semiconductor device as claimed in claim 4, wherein the electrode layer is connected to one power supply potential of the semiconductor device.

7. (Amended) The semiconductor device as claimed in claim 1, further comprising:

a source electrode and a drain electrode formed on the active layer, separated from each other so as to establish a channel region, and

Sub C1 > B1

a gate electrode formed above the channel region.

Sub C1 > B2

8. (Twice Amended) The semiconductor device as claimed in claim 7, wherein the active layer has 2-Dimensional Electron Gasses.

Sub C1 > B3

9. (Amended) The semiconductor device as claimed in claim 1, wherein the active layer comprises:

a collector layer of a first conducting type;

a base layer of a second conducting type formed on the collector layer;

an emitter layer of the first conducting type formed on the base layer.

10. (Amended) The semiconductor device as claimed in claim 1, wherein the compound semiconductor substrate has a resistivity more than 1.0×10^8 Ohm-cm in total.